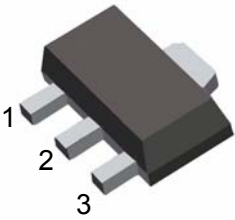


TRANSISTOR (PNP)																																																																												
<p style="text-align: center;"><u>SOT-89</u></p> <p>1. BASE</p> <p>2. COLLECTOR</p> <p>3. EMITTER</p> 		<p>Features</p> <ul style="list-style-type: none"> • Low $V_{CE(sat)}$: -0.2V(Typ) $I_C/I_B=-500mA/-50mA$ • Compliments 2SD1664 <p>MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)</p> <table border="1"> <thead> <tr> <th>Symbol</th> <th>Parameter</th> <th>Value</th> <th>Units</th> </tr> </thead> <tbody> <tr> <td>V_{CBO}</td> <td>Collector-Base Voltage</td> <td>-40</td> <td>V</td> </tr> <tr> <td>V_{CEO}</td> <td>Collector-Emitter Voltage</td> <td>-32</td> <td>V</td> </tr> <tr> <td>V_{EBO}</td> <td>Emitter-Base Voltage</td> <td>-5</td> <td>V</td> </tr> <tr> <td>I_C</td> <td>Collector Current -Continuous</td> <td>-1</td> <td>A</td> </tr> <tr> <td>P_C</td> <td>Collector Power Dissipation</td> <td>500</td> <td>mW</td> </tr> <tr> <td>T_J</td> <td>Junction Temperature</td> <td>150</td> <td>$^\circ\text{C}$</td> </tr> <tr> <td>T_{stg}</td> <td>Storage Temperature</td> <td>-55-150</td> <td>$^\circ\text{C}$</td> </tr> </tbody> </table>					Symbol	Parameter	Value	Units	V_{CBO}	Collector-Base Voltage	-40	V	V_{CEO}	Collector-Emitter Voltage	-32	V	V_{EBO}	Emitter-Base Voltage	-5	V	I_C	Collector Current -Continuous	-1	A	P_C	Collector Power Dissipation	500	mW	T_J	Junction Temperature	150	$^\circ\text{C}$	T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$																																						
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Typical Characteristics

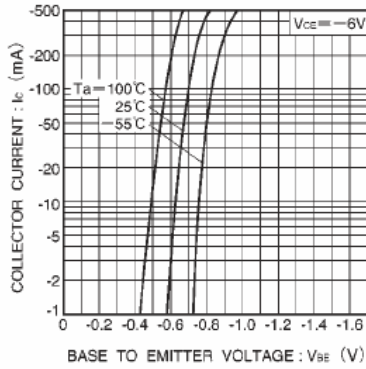


Fig.1 Grounded emitter propagation characteristics

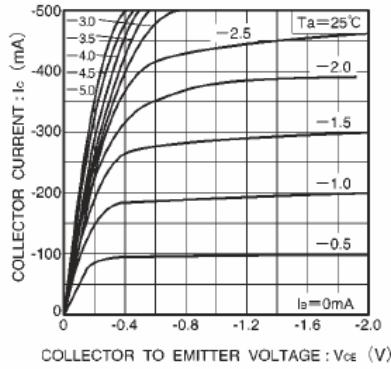


Fig.2 Grounded emitter output characteristics

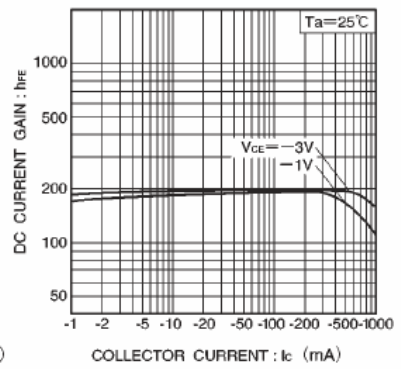


Fig.3 DC current gain vs. collector current (I)

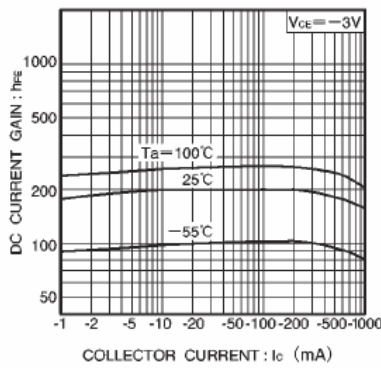


Fig.4 DC current gain vs. collector current (II)

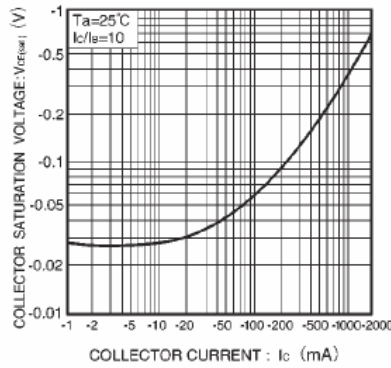


Fig.5 Collector-emitter saturation voltage vs. collector current

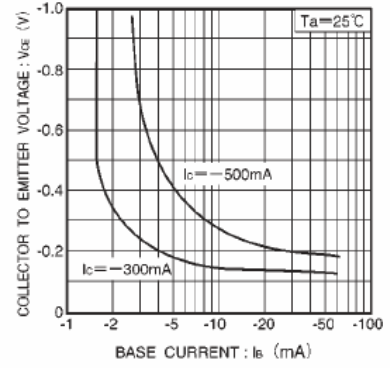


Fig.6 Collector-emitter saturation voltage vs. base current

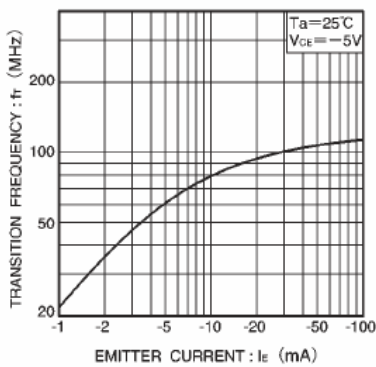


Fig.7 Gain bandwidth product vs. emitter current

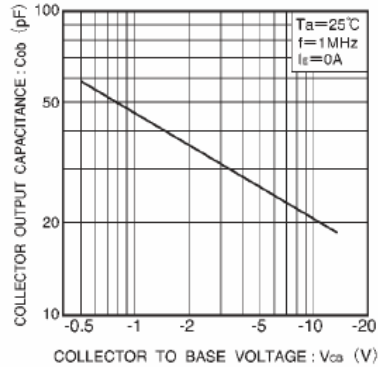


Fig.8 Collector output capacitance vs. collector-base voltage

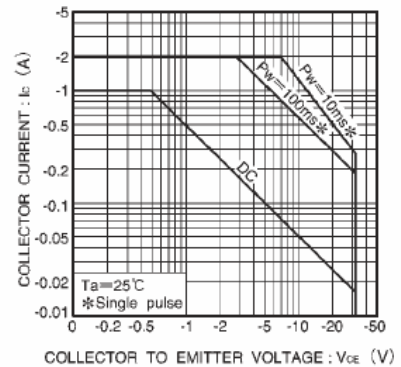


Fig.9 Safe operation area

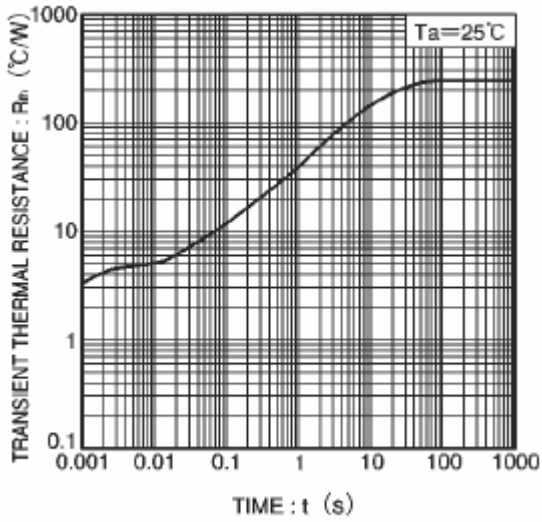


Fig.10 Transient thermal resistance

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)